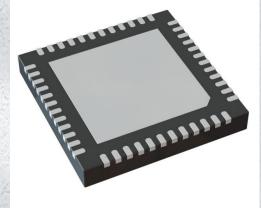


# PI6CG33802CZLIEX Datasheet

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DiGi Electronics Part Number
Manufacturer
Aanufacturer Product Number
Description
Detailed Description

PI6CG33802CZLIEX-DG
Diodes Incorporated

PI6CG33802CZLIEX

IC CLOCK GENERATOR 48TQFN

Clock Generator IC 100MHz 1 48-VFQFN Exposed Pa d

https://www.DiGi-Electronics.com



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# Purchase and inquiry

Manufacturer:
Diodes Incorporated
Product Status:
Active
Type:
Clock Generator
Input:
CMOS, Crystal
Number of Circuits:
1
Frequency - Max:
100MHz
Voltage - Supply:
3.135V ~ 3.465V
Mounting Type:
Surface Mount
Supplier Device Package:
48-TQFN (6x6)

# **Environmental & Export classification**

RoHS Status:	Moisture Sensitivity Level (MSL):
ROHS3 Compliant	1 (Unlimited)
REACH Status:	ECCN:
REACH Unaffected	EAR99
HTSUS:	
8542.39.0001	





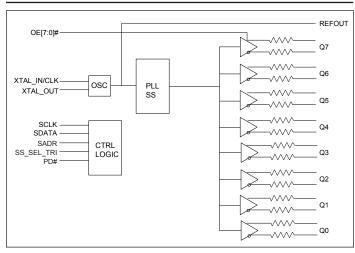
#### 3.3V Very Low Power 8-Output PCIe Clock Generator With On-Chip Termination

## Description

The DIODES PI6CG33802C is an 8-output, very-low-power PCIe Gen1/Gen2/Gen3/Gen4/Gen5/Gen6 clock generator. It uses a 25MHz crystal or CMOS reference as an input to generate the 100MHz low-power differential HCSL outputs with on-chip terminations. The on-chip termination can save 32 external resistors and make layout easier. An additional buffered reference output is provided to serve as a low-noise reference for other circuitry.

It uses Diodes' proprietary PLL design to achieve very-low jitter that meets PCIe Gen1/Gen2/Gen3/Gen4/Gen5/Gen6 requirements. It also provides various options, such as different slew rate and amplitude through SMBUS, so users can easily configure the device to get the optimized performance for their individual boards. The device also supports selectable spreadspectrum options to reduce EMI for various applications.

## **Block Diagram**



#### Features

- 3.3V Supply Voltage •
- Crystal/CMOS Input: 25 MHz
- Eight Differential Low-Power HCSL Outputs with On-Chip Termination
- Default  $Z_{OUT} = 85\Omega$
- Individual Output Enable •
- Reference CMOS Output
- Programmable Slew Rate and Output Amplitude for Each Output
- Differential Outputs Blocked Until PLL is Locked •
- Selectable 0%, -0.25%, or -0.5% Spread on Differential Outputs
- Strapping Pins or SMBus for Configuration •
- . Differential Output-To-Output Skew <60ps
- Very-Low Jitter Outputs
  - Differential Cycle-To-Cycle Jitter <50ps</li>
  - PCIe Gen1/Gen2/Gen3/Gen4/Gen5/Gen6 Compliant
  - CMOS REFOUT Phase Jitter
    - <0.3ps RMS, SSC off
    - <1.5ps RMS, SSC on
- Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3) •
- For automotive applications requiring specific change control (i.e. parts qualified to AEC-Q100/101/104/200, PPAP capable, and manufactured in IATF 16949 certified facilities), please contact us or your local Diodes representative.

https://www.diodes.com/quality/product-definitions/

Packaging (Pb-free & Green): □ 48-lead 6mm × 6mm TQFN

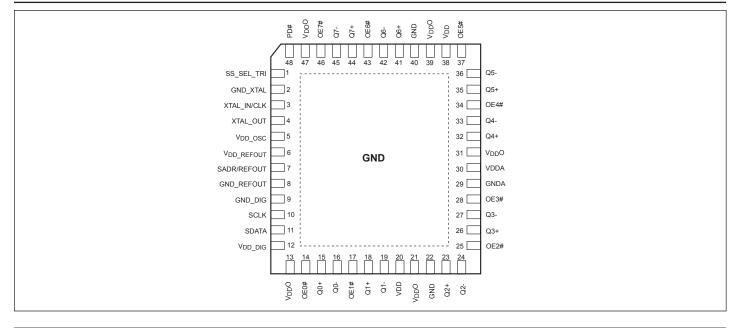
#### Notes:

- 1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS), 2011/65/EU (RoHS 2) & 2015/863/EU (RoHS 3) compliant.
- 2. See https://www.diodes.com/quality/lead-free/ for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free. 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.





## **Pin Configuration**



## **Pin Description**

Pin #	Pin Name	Ту	pe	Description	
				Latched select input to select spread spectrum amount at initial power up.	
1	SS_SEL_TRI	Input	Tri-level	$1 = -0.5\%$ spread, M = Spread Off, 0 = Spread Off. This pin has both internal pull-up and pull-down. Refer to SMBUS byte_1 bit 4, 3 = '01' to get -0.25% spread.	
2	GND_XTAL	Power		Ground for oscillator circuit	
3	XTAL_IN/CLK	Input		Crystal input or CMOS reference input	
4	XTAL_OUT	Output		Crystal output	
5	V <sub>DD</sub> _OSC	Power		Power supply for oscillator circuitry, nominal 3.3V	
6	V <sub>DD</sub> _REFOUT	Power		Power supply for buffered CMOS output	
7	SADR/REFOUT	Input/ Output	CMOS	Latch to select SMBus Address or LVCMOS REFOUT. This pin has an internal pull-down	
8	GND_REFOUT	Power		Ground for REFOUT	
9	GND_DIG	Power		Ground for digital circuitry	
10	SCLK	Input	CMOS	SMBUS clock input, 3.3V tolerant	
11	SDATA	Input/ Output	CMOS	SMBUS data line, 3.3V tolerant	
12	V <sub>DD</sub> _DIG	Power		Power supply for digital circuitry, nominal 3.3V	
13, 21, 31, 39, 47	V <sub>DDO</sub>	Power		Power supply for differential outputs	
14	OE0#	Input	CMOS	Active-low input for enabling Q0 pair. This pin has an internal pulldown. 1 = disable outputs, $0 = $ enable outputs	





Pin #	Pin Name	Ту	pe	Description
15	Q0+	Output	HCSL	Differential true clock output
16	Q0-	Output	HCSL	Differential complementary clock output
17	OE1#	Input	CMOS	Active low input for enabling Q1 pair. This pin has an internal pulldown. 1 = disable outputs, 0 = enable outputs
18	Q1+	Output	HCSL	Differential true clock output
19	Q1-	Output	HCSL	Differential complementary clock output
20, 38	V <sub>DD</sub>	Power		Power supply, nominal 3.3V
22, 40	GND	Power		Ground
23	Q2+	Output	HCSL	Differential true clock output
24	Q2-	Output	HCSL	Differential complementary clock output
25	OE2#	Input	CMOS	Active low input for enabling Q2 pair. This pin has an internal pulldown. 1 = disable outputs, $0 = $ enable outputs
26	Q3+	Output	HCSL	Differential true clock output
27	Q3-	Output	HCSL	Differential complementary clock output
28	OE3#	Input	CMOS	Active low input for enabling Q3 pair. This pin has an internal pulldown. 1 = disable outputs, $0 = $ enable outputs
29	GNDA	Power		Ground for analog circuitry
30	V <sub>DDA</sub>	Power		Power supply for analog circuitry
32	Q4+	Output	HCSL	Differential true clock output
33	Q4-	Output	HCSL	Differential complementary clock output
34	OE4#	Input	CMOS	Active low input for enabling Q4 pair. This pin has an internal pulldown. 1 = disable outputs, $0 = $ enable outputs
35	Q5+	Output	HCSL	Differential true clock output
36	Q5-	Output	HCSL	Differential complementary clock output
37	OE5#	Input	CMOS	Active low input for enabling Q5 pair. This pin has an internal pulldown. 1 = disable outputs, $0 = $ enable outputs
41	Q6+	Output	HCSL	Differential true clock output
42	Q6-	Output	HCSL	Differential complementary clock output
43	OE6#	Input	CMOS	Active low input for enabling Q6 pair. This pin has an internal pulldown. 1 = disable outputs, $0 = $ enable outputs
44	Q7+	Output	HCSL	Differential true clock output
45	Q7-	Output	HCSL	Differential complementary clock output
46	OE7#	Input	CMOS	Active low input for enabling Q7 pair. This pin has an internal pulldown. 1 = disable outputs, 0 = enable outputs
48	PD#	Input	CMOS	Input notifies device to sample latched inputs and start up on first high assertion. Low enters Power Down Mode, subsequent high assertions exit Power Down Mode. This pin has internal pull-up resistor.





#### **Table 1. SMBus Address Selection Table**

	SADR	Address	+Read/Write Bit
State of CADD on first and listing of DD#	0	1101000	Х
State of SADR on first application of PD#	1	1101010	Х

## Table 2. Power Management Table<sup>(3)</sup>

PD#	SMBus OE bit	SMBus OE bit OEn# C		Qn-	REFOUT
0	Х	X X Low <sup>(1)</sup> Low <sup>(1)</sup>		Low <sup>(1)</sup>	HiZ <sup>(2)</sup>
1	1	0	Running	Running	Running
1	1	1 Disabled <sup>(1)</sup> Disabled <sup>(1)</sup>		Running	
1	0	Х	Disabled <sup>(1)</sup>	Disabled <sup>(1)</sup>	Disabled <sup>(4)</sup>

#### Notes:

1. The output state is set by B11[1:0] (Low/Low default).

2. REF is Hi-Z until the first assertion of PD# high. After this, when PD# is low, REF is disabled. If Byte3, bit 5 = 1, REF is running.

Input High/ Low defined at default values for device. 3.

4. See SMBUs Byte 3, bit 4.





## **Maximum Ratings**

(Above which useful life may be impaired. For user guidelines, not tested.)	
Storage Temperature65°C to +150°C	Note:
Supply Voltage to Ground Potential, V <sub>DDxx</sub> 0.5V to +4.6V	Stresses greater than those listed under MAXIMUM RATINGS
Input Voltage $-0.5V$ to V <sub>DD</sub> +0.5V, not exceed 4.6V	may cause permanent damage to the device. This is a stress rating only and functional operation of the device at these or
SMBus, Input High Voltage 3.6V	any other conditions above those indicated in the operational
ESD Protection (HBM)	sections of this specification is not implied. Exposure to ab-
Max Junction Temperature+125°C	solute maximum rating conditions for extended periods may affect reliability.

## **Operating Conditions**

Temperature = T<sub>A</sub>; Supply voltages per normal operation conditions; See test circuits for the load conditions

Symbol	Parameters	Conditions	Min.	Тур.	Max.	Units
V <sub>DD</sub> , V <sub>DDA</sub> , V <sub>DD</sub> OSC, V <sub>DD</sub> DIG,	Power Supply Voltage		3.135	3.3	3.465	V
V <sub>DDO</sub>	Output Power Supply Voltage		1.0	3.3	3.465	V
V <sub>DD_REFOUT</sub>	Reference Output Power Supply Voltage		3.135	3.3	3.465	V
I <sub>DDA</sub>	Analog Power Supply Current	All outputs active @100MHz		22	25	mA
I <sub>DD</sub>	Power Supply Current	All $V_{DD}$ , except $V_{DDA}$ and $V_{DDO}$ , All outputs active @100MHz		20	25	mA
I <sub>DDO</sub>	Power Supply Current for Outputs <sup>(3)</sup>	All outputs active @100MHz		29	34	mA
I <sub>DDA_WL</sub>	Analog Power Supply Wake-on- LAN <sup>(1)</sup> Current	Q outputs off, REF output run- ning		0.5	1	mA
I <sub>DD_WL</sub>	Power Supply Wake-on-LAN <sup>(1)</sup> Current	All $V_{DD}$ , except $V_{DDA}$ and $V_{DDO}$ , Q outputs off, REF output running		3	6	mA
I <sub>DDO_WL</sub>	Power Supply Wake-on-LAN <sup>(1)</sup> Current for Outputs	Q outputs off, REF output run- ning		0.04	0.1	mA
I <sub>DDA_PD</sub>	Analog Power Supply Power Down <sup>(2)</sup> Current	All outputs off		0.5	1	mA
I <sub>DD_PD</sub>	Power Supply Power Down <sup>(2)</sup> Current	All outputs off		1	2	mA
I <sub>DDO_PD</sub>	Power Supply Current Power Down <sup>(2)</sup> for Outputs	All outputs off		0.05	0.1	mA
T <sub>A</sub>	Ambient Temperature	Industrial grade	-40		85	°C

Notes:

1. Wake-on-LAN mode: PD# = '0' Byte 3, bit 5 = '1'.

2. Power down mode: PD# = '0' Byte 3, bit 5 = '0'.

3. Output drive 5 inch trace.





## **Input Electrical Characteristics**

Symbol	Parameters	Conditions	Min.	Тур.	Max.	Units
R <sub>pu</sub>	Internal Pullup Resistance			120		ΚΩ
R <sub>dn</sub>	Internal Pulldown Resistance			120		ΚΩ
C <sub>XTAL</sub>	Internal Capacitance on X_IN and X_OUT pins			8		pF
L <sub>PIN</sub>	Pin Inductance				7	nH

## **Crystal Characteristic**

Parameters	Description	Min.	Тур	Max.	Units
OSCmode	Mode of Oscillation	F	undamenta	al	
FREQ	Frequency		25		MHz
ESR <sup>(1)</sup>	Equivalent Series Resistance			50	Ω
Cload	Load Capacitance		8		pF
Cshunt	Shunt Capacitance			7	pF
	Drive Level			200	uW

Note:

1. ESR value is dependent upon frequency of oscillation.

## **SMBus Electrical Characteristics**

Temperature =	Temperature = $T_A$ ; Supply voltages per normal operation conditions; See test circuits for the load conditions							
Symbol	Parameters	Conditions	Min.	Тур.	Max.	Units		
V <sub>DDSMB</sub>	Nominal bus voltage		2.7		3.6	V		
		SMBus, $V_{DDSMB} = 3.3V$	2.1		3.6			
V <sub>IHSMB</sub>	SMBus Input High Voltage	SMBus, V <sub>DDSMB</sub> < 3.3V	0.65 V <sub>DDSMB</sub>			V		
37		SMBus, V <sub>DDSMB</sub> = 3.3V			0.8	V		
V <sub>ILSMB</sub>	SMBus Input Low Voltage	SMBus, V <sub>DDSMB</sub> < 3.3V			0.8			
I <sub>SMBSINK</sub>	SMBus Sink Current	SMBus, at V <sub>OLSMB</sub>	4			mA		
VOLSMB	SMBus Output Low Voltage	SMBus, at I <sub>SMBSINK</sub>			0.4	V		
f <sub>MAXSMB</sub>	SMBus Operating Frequency	Maximum frequency			500	kHz		
t <sub>RMSB</sub>	SMBus Rise Time	(Max V <sub>IL</sub> - 0.15) to (Min V <sub>IH</sub> + 0.15)			1000	ns		
t <sub>FMSB</sub>	SMBus Fall Time	(Min V <sub>IH</sub> + 0.15) to (Max V <sub>IL</sub> - 0.15)			300	ns		





## **Spread Spectrum Characteristic**

Temperature = T<sub>A</sub>; Supply voltages per normal operation conditions; See test circuits for the load conditions

Symbol		Conditions	Min.	Тур.	Max.	Units
f <sub>MOD</sub>	SS Modulation Frequency	Triangular modulation	30	31.8	33	kHz

## **LVCMOS DC Electrical Characteristics**

Temperature = T<sub>A</sub>; Supply voltages per normal operation conditions; See test circuits for the load conditions

Symbol	Parameters	Conditions	Min.	Тур.	Max.	Units
V <sub>IH</sub>	Input High Voltage	Single-ended inputs, except SMBus	0.75 V <sub>DD</sub>		V <sub>DD</sub> + 0.3	V
V <sub>IM</sub>	Input Mid Voltage	SS_SEL_TRI	$0.4 V_{DD}$	$0.5 V_{DD}$	$0.6V_{DD}$	V
V <sub>IL</sub>	Input Low Voltage	Single-ended inputs, except SMBus	-0.3		0.25 V <sub>DD</sub>	V
I <sub>IH</sub>	Input High Current	Single-ended inputs, $V_{IN} = V_{DD}$			5	μΑ
I <sub>IL</sub>	Input Low Current	Single-ended inputs, $V_{IN} = 0V$	-5			μΑ
I <sub>IH</sub>	Input High Current	Single-ended inputs with pullup/ pulldown resistor, $V_{\rm IN}$ = $V_{\rm DD}$			50	μΑ
I <sub>IL</sub>	Input Low Current	Single-ended inputs with pullup/ pulldown resistor, $V_{IN} = 0V$	-50			μΑ
V <sub>OH</sub>	Output High Voltage	REFOUT, except SMBus; I <sub>OH</sub> = -2mA	$0.8 \times V_{DD_{-}}$ Refout			V
V <sub>OL</sub>	Output Low Voltage	REFOUT, except SMBus; I <sub>OL</sub> = 2mA			$0.2 \times V_{DD_{-}}$ Refout	V
R <sub>OUT</sub>	CMOS Output impedance			20		Ω
C <sub>IN</sub>	Input Capacitance		1.5		5	pF

## **LVCMOS AC Characteristics**

Temperature = T<sub>A</sub>; Supply voltages per normal operation conditions; See test circuits for the load conditions.

Symbol	Parameters	Conditions	Min.	Тур.	Max.	Units
f <sub>INPUT</sub>	Input Frequency	XTAL_IN/CLK		25		MHz
t <sub>RIN</sub>	Input Rise Time	Single-ended inputs			5	ns
t <sub>FIN</sub>	Input fall time	Single-ended inputs			5	ns
t <sub>STAB</sub>	Clock Stabilization	From power up and after input clock stabilization or deassertion of PD# to first clock		0.75	1	ms
t <sub>OELAT</sub>	Output Enable Latency	Q start after OE# assertion Q stop after OE# deassertion	1		3	clocks





Symbol	Parameters	Conditions	Min.	Тур.	Max.	Units
t <sub>PDLAT</sub>	PD# Deassertion	Differential outputs enable after PD# deassertion		20	300	μs
t <sub>PERIOD</sub>	REFOUT Clock Period	REFOUT, assume input is at 25MHz		40		ns
f <sub>ACC</sub>	REFOUT Frequency Accuracy <sup>(1)</sup>	REFOUT, long term accuracy to input		0		ppm
		Byte 3 = 1F, 20% to 80% of V <sub>D</sub> . DREF	0.9	1.4	2	V/ns
	REFOUT Slew Rate <sup>(1)</sup>	Byte 3 = 5F, 20% to 80% of $V_{D}$ -DREF	1.5	2.4	3.2	V/ns
t <sub>SLEW</sub>	REFOUT Siew Rate	Byte 3 = 9F, 20% to 80% of V <sub>D</sub> . DREF	2.0	3.0	3.8	V/ns
		Byte 3 = DF, 20% to 80% of $V_{D}$ . DREF	2.3	3.2	4	V/ns
t <sub>DC</sub>	REFOUT Duty Cycle <sup>(1)</sup>	$V_{\rm T} = V_{\rm DD}/2V$ , driven by a Xtal	45	50	55	%
t <sub>DCDIS</sub>	REFOUT Duty Cycle Distortion	$V_T = V_{DD}/2V$ , driven by an external source	-2	0	+2	%
t <sub>JITCC</sub>	REFOUT Cycle-Cycle Jitter	$V_{\rm T} = V_{\rm DD}/2V$ , driven by a Xtal		70	150	ps
		12kHz to 5MHz, SSC off, driven by a Xtal		0.16	0.3	ps
tJITPH	REFOUT Phase Jitter, RMS	12kHz to 5MHz, SSC on, driven by a Xtal		0.9	1.5	ps
		1kHz offset, driven by a Xtal		-149	-135	dBc/Hz
t <sub>JITN</sub>	Noise Floor	10kHz offset to Nyquist, driven by a Xtal		-158	-140	dBc/Hz

#### Note:

1. Guaranteed by design and characterization—not 100% tested in production.





## **HCSL Output Characteristics**

Temperature =  $T_A$ ; Supply voltages per normal operation conditions; See test circuits for the load conditions.

Symbol	Parameters	Condition	Min.	Тур.	Max.	Units
V <sub>OH</sub>	Output Voltage High <sup>(1)</sup>	Statistical measurement on	660	784	850	mV
V <sub>OL</sub>	Output Voltage Low <sup>(1)</sup>	single-ended signal using oscil- loscope math function	-150		150	mV
V <sub>OMAX</sub>	Output Voltage Maximum <sup>(1)</sup>	Measurement on single-ended		816	1150	mV
V <sub>OMIN</sub>	Output Voltage Minimum <sup>(1)</sup>	signal using absolute value	-300	-42		mV
V <sub>OC</sub>	Output Cross Voltage <sup>(1,2,4)</sup>		250	430	550	mV
DV <sub>OC</sub>	V <sub>OC</sub> Magnitude Change <sup>(1,2,5)</sup>			12	140	mV

Note:

- 1. At default SMBUS amplitude settings.
- Guaranteed by design and characterization-not 100% tested in production. 2.

Measured from differential waveform. 3.

- This one is defined as voltage where  $Q_{+} = Q_{-}$  measured on a component test board and only applied to the differential rising edge. 4.
- The total variation of all Vcross measurements in any particular system. This is a subset of Vcross\_min/max allowed. 5.

## **HCSL Output AC Characteristics**

Temperature =  $T_A$ ; Supply voltages per normal operation conditions; See test circuits for the load conditions

Symbol	Parameters	Condition	Min.	Тур.	Max.	Units
f <sub>OUT</sub>	Output Frequency			100		MHz
	Slew Rate <sup>(1,2,3)</sup>	Scope averaging on fast setting	2.5	3.2	4	V/ns
t <sub>RF</sub>	Slew Rate	Scope averaging on slow setting	2.2	3	3.7	V/ns
Dt <sub>RF</sub>	Slew Rate Matching <sup>(1,2,4)</sup>	Scope averaging on		7	15	%
t <sub>DC</sub>	Duty Cycle <sup>(1,2)</sup>	Measured differentially, PLL Mode	45	50	55	%
t <sub>SKEW</sub>	Output Skew <sup>(1,2)</sup>	Averaging on, $V_T = 50\%$		20	60	ps
tj <sub>c-c</sub>	Cycle-to-Cycle Jitter <sup>(1,2)</sup>			20	50	ps

Note:

1. Guaranteed by design and characterization—not 100% tested in production.

Measured from differential waveform. 2.

Slew rate is measured through the Vswing voltage range centered around differential 0V, within ±150mV window. 3.

It is measured using a ±75mV window centered on the average cross point. 4.





## PCIe Common Clock (CC) Architecture Jitter

Symbol	Parameters	Condition	Min.	Тур.	Max.	Spec Limit	Units
		PCIe 1.0		20	30	86	ps (pkpk)
		PCIe 2.0 Low Band, 10kHz < f < 1.5MHz (PLL BW 5-16MHz or 8-5MHz, CDR = 10MHz)		0.1	0.2	3	ps
tjphase	Integrated phase jitter (RMS)	PCIe 2.0 High Band, 1.5MHz < f < Nyquist (50MHz); (PLL BW 5-16MHz or 8-5MHz, CDR = 10MHz)		0.4	0.5	3.1	ps
		PCIe 3.0 (PLL BW 2-4MHz or 2-5MHz, CDR = 10MHz)		0.15	0.2	1	ps
		PCIe 4.0 (PLL BW 2-4MHz or 2-5MHz, CDR = 10MHz)		0.15	0.2	0.5	ps
		PCIe 5.0		0.05	0.06	0.15	ps
		PCIe 6.0		0.03	0.04	0.1	ps

## PCIe Independent Reference Clock Architecture Jitter

Symbol	Parameters	Condition	Min.	Тур.	Max.	Spec Limit	Units
		PCIe 3.0 SRIS (PLL BW 2-4MHz or 2-5MHz, CDR = 10MHz)		0.15	0.25		ps
t <sub>jPHASE</sub>	Integrated phase jitter (RMS)	PCIe 4.0 SRIS (PLL BW 2-4MHz or 2-5MHz, CDR = 10MHz)		0.15	0.25		ps
		PCIe 5.0 SRIS		0.04	0.07		ps
		PCIe 6.0 SRIS		0.03	0.05		ps





## **Differential Output Clock Periods - Spread Spectrum Disabled**

			Mea	asurement Win	dow				
Center	1 clock	1µs	0.1s	0.1s	0.1s	1µs	1 clock		
Freq. MHz	-c2c jitter AbsPer Min	-SSC Short- term Avg. Min	-ppm Long- term Avg. Min	0 ppm Pe- riod Nomi- nal	+ppm Long- term Avg. Max	+SSC Short- term Avg. Max	-c2c jitter AbsPer Max	Units	
100.00	9.94900		9.99900	10.00000	10.00100		10.05100	ns	

## **Differential Output Clock Periods - Spread Spectrum Enabled**

			Mea	asurement Win	dow			
Center	1 clock	1µs	0.1s	0.1s	0.1s	1µs	1 clock	
Freq. MHz	-c2c jitter AbsPer Min	-SSC Short- term Avg. Min	-ppm Long- term Avg. Min	0 ppm Pe- riod Nomi- nal	+ppm Long- term Avg. Max	+SSC Short- term Avg. Max	-c2c jitter AbsPer Max	Units
99.75	9.94906	9.99906	10.02406	10.02506	10.02607	10.05107	10.10107	ns

Note:

1. Guaranteed by design and characterization—not 100% tested in production

2. All long-term accuracy and clock period specifications are guaranteed assuming REF is trimmed to 25.00MHz.





## **SMBus Serial Data Interface**

PI6CG33802C is a slave only device that supports block read and block write protocol using a single 7-bit address and read/write bit as shown below.

Read and write block transfers can be stopped after any complete byte transfer.

#### **Address Assignment**

A6	A5	A4	A3	A2	A1	A0	R/W
1	1	0	1	0	SADR	0	1/0

Note:

1. SMBus address is latched on SADR pin.

#### How to Write

1 bit	7 bits	1 bit	1 bit	8 bits	1 bit	8 bits	1 bit	8 bits	1 bit	8 bits	1 bit	1 bit
Start bit	Add.	W(0)	Ack	Beginning Byte loca- tion = N	Ack	Data Byte count = X	Ack	Beginning Data Byte (N)	Ack	 Data Byte (N+X-1)	Ack	Stop bit

#### How to Read

1 bit	7 bits	1 bit	1 bit	8 bits	1 bit	1 bit	7 bits	1 bit	1 bit	8 bits	1 bit	8 bits	1 bit
Start bit	Address	W(0)	Ack	Beginning Byte loca- tion = N	Ack	Repeat Start bit	Address	R(1)	Ack	Data Byte count = X	Ack	Beginning Data Byte (N)	Ack

8 bits	1 bit	1 bit
Data Byte	NAck	Stop bit
(N+X-1)	INACK	5100 011

Byte (	Byte 0: Output Enable Register									
Bit	Control Function	Description	Туре	Power-up Condition	0	1				
7	Q7_OE	Q7 output enable	RW	1		Pin Control				
6	Q6_OE	Q6 output enable	RW	1		Pin Control				
5	Q5_OE	Q5 output enable	RW	1		Pin Control				
4	Q4_OE	Q4 output enable	RW	1	C D11[1.0]	Pin Control				
3	Q3_OE	Q3 output enable	RW	1	See B11[1:0]	Pin Control				
2	Q2_OE	Q2 output enable	RW	1		Pin Control				
1	Q1_OE	Q1 output enable	RW	1		Pin Control				
0	Q0_OE	Q0 output enable	RW	1		Pin Control				

Note:

1. A low on these bits will override the OE# pins and force the differential outputs to the state indicated by B11[1:0] (Low/ Low default).





Byte 1	: SS Spread Spectrum	and Control Register				
Bit	Control Function	Description	Туре	Power-up Condition	0	1
7	SSENRB1	SS Enable Readback Bit1	R	Latch	'00' for SS_SEL	_TRI = '0',
6	SSENRB0	SS Enable Readback Bit0	R	Latch	'10' for SS_SEL_TRI = 'M' '11' for SS_SEL_TRI = '1'	
5	SSEN_SWCTR	Enable SW control of SS	RW	0	Values in B1[7:6] control SS amount	Values in B1[4:3] control SS amount
4	SSENSW1	SS enable SW control Bit1	RW <sup>(1)</sup>	0	'00' = SS off, '01	' = -0.25% SS,
3	SSENSW0	SS enable SW control Bit0	RW <sup>(1)</sup>	0	'10' = SS off, '11'	= -0.5% SS
2	Reserved			1		
1	Amplitude1	- Control output amplitudo	RW	1	'00' = 0.6V, '01' =	= 0.68V, '10' =
0	Amplitude0	Control output amplitude	RW	0	0.75V, '11' = 0.85	5V

Note:

Spread must be selected OFF or ON with the hardware latch pin. These bits should not be used to turn spread ON or OFF after power up. These bits can be used to 1. change the spread amount, and B1[5] must be set to a 1 for these bits to have any effect on the part. If these bits are used to turn spread OFF or ON, the system must reset.

Byte 2	Byte 2: Differential Output Slew Rate Control Register									
Bit	Control Function	Description	Туре	Power-up Condition	0	1				
7	SLEWRATECTR_Q7	Control slew rate of Q7	RW	1	Slow setting	Fast setting				
6	SLEWRATECTR_Q6	Control slew rate of Q6	RW	1	Slow setting	Fast setting				
5	SLEWRATECTR_Q5	Control slew rate of Q5	RW	1	Slow setting	Fast setting				
4	SLEWRATECTR_Q4	Control slew rate of Q4	RW	1	Slow setting	Fast setting				
3	SLEWRATECTR_Q3	Control slew rate of Q3	RW	1	Slow setting	Fast setting				
2	SLEWRATECTR_Q2	Control slew rate of Q2	RW	1	Slow setting	Fast setting				
1	SLEWRATECTR_Q1	Control slew rate of Q1	RW	1	Slow setting	Fast setting				
0	SLEWRATECTR_Q0	Control slew rate of Q0	RW	1	Slow setting	Fast setting				





Byte 3	Byte 3: REF Control Register									
Bit	Control Function	Description	Туре	Power-up Condition	0	1				
7		Slew rate control for REF	RW 0		'00' = 1.4V/ns '0	01' = 2.4V/ns,				
6	REFSLEWRATE	Siew rate control for REF	RW	1	'10' = 3V/ns, '11' = 3.2V/ns					
5	REF_PDSTATE	Wake-on-Lan enable for REF	RW	0	REF = Disabled in PD state <sup>(1)</sup>	REF = running in PD state				
4	REF_OE	Output enable for REF	RW	1	REF = Disabled <sup>(1)</sup>	REF = running				
3	Reserved			1						
2	Reserved			1						
1	Reserved			1						
0	Reserved			1						

Note:

1. The disabled state depends on Byte11[1:0]. '00' = Low, '01'=HiZ, '10'=Low, '11'=High.

Byte 4: Reserved									
Bit	Control Function	Description	Туре	Power-up Condition	0	1			
7:0	Reserved			0x40					

#### Byte 5: Revision and Vendor ID Register

Bit	Control Function	Description	Туре	Power-up Condition	0 1		
7	RID3		R	0	- Rev = 0000		
6	RID2		R	0			
5	RID1	Revision ID	R	0			
4	RID0		R	0			
3	PVID3		R	0			
2	PVID2		R	0			
1	PVID1	- Vendor ID	R	1	Diodes = 0011		
0	PVID0		R	1	-		





Bit	<b>Control Function</b>	Description	Туре	Power-up Condition	0	1	
7	DTYPE1		R	0	'00' = CG, '01	' = ZDB,	
6	DTYPE0	<ul> <li>Device type</li> </ul>	R	0	-	ed, '11' = NZDB	
5	DID5		R	0			
4	DID4		R	0	=		
3	DID3	_	R	1			
2	DID2	- Device ID	R	0	001000 binary, 08Hex		
1	DID1		R	0			
0	DID0		R	0			
Byte 7	: Byte Count Register		1		L		
Bit	Control Function	Description	Туре	Power-up Condition	0	1	
7	Reserved			0			
6	Reserved			0			
5	Reserved			0			
4	BC4		RW	0			
3	BC3		RW	1	Writing to th	is register will	
2	BC2	Byte count programming	RW	0		w many bytes will	
1	BC1		RW	0	be read back, default is 8 byt		
0	BC0		RW	0			
Byte 8	and 9: Reserved				<u>.</u>		
Bit	Control Function	Description	Туре	Power-up Condition	0	1	
7.0	D 1			B8 = 0x36			
7:0	Reserved			B9 = 0x00			
Byte 1	0: PD Restore						
Bit	Control Function	Description	Туре	Power-up Condition	0	1	
7	Reserved			0			
6	PD Restore	PD restore to default configuration	RW	1	Clear PD Config	Keep PD Config	
5:0	Reserved			0			





Byte 1	1: Stop Control					
Bit	Control Function	Description	Туре	Power-up Condition	0	1
7:2	Reserved			0		
1	STP1		RW	0	00 = Low/Low	10 = High/ Low
0	STP0	True/ Compliment DIF Output Disable Sate	RW	0	01 = HiZ/HiZ	11 = Low/ High
Byte 1	2: Impedance Control					
Bit	Control Function	Description	Туре	Power-up Condition	0	1
7	Q3_Zout1	Q3 Zout	RW			1
6	Q3_Zout0	Q3 Zout	RW			
5	Q2_Zout1	Q2 Zout	RW		00 = Reserved	
4	Q2_Zout0	Q2 Zout	RW	01	$01 = 85\Omega$	
3	Q1_Zout1	Q1 Zout	RW	- 01	$10 = 100\Omega$	
2	Q1_Zout0	Q1 Zout	RW		11 = Reserved	
1	Q0_Zout1	Q0 Zout	RW			
0	Q0_Zout0	Q0 Zout	RW			
Byte 1	3: Impedance Control					
Bit	Control Function	Description	Туре	Power-up Condition	0	1
7	Q7_Zout1	Q7 Zout	RW			
6	Q7_Zout0	Q7 Zout	RW			
5	Q6_Zout1	Q6 Zout	RW		00 = Reserved	
4	Q6_Zout0	Q6 Zout	RW	01	$01 = 85\Omega$	
3	Q5_Zout1	Q5 Zout	RW	01	$10 = 100\Omega$	
2	Q5_Zout0	Q5 Zout	RW		11 = Reserved	
1	Q4_Zout1	Q4 Zout	RW			
0	Q4_Zout0	Q4 Zout	RW			





Byte 14	4: OE Termination Co	ntrol				
Bit	Control Function	Description	Туре	Power-up Condition	0	1
7	OE3_term1	OE3 Pullup or down	RW	0	00 = None	10 = Pullup
6	OE3_term0	OE3 Pullup or down	RW	1	01 = Pull- down	11 = Pullup and Down
5	OE2_term1	OE2 Pullup or down	RW	0	00 = None	10 = Pullup
1	OE2_term0	OE2 Pullup or down	RW	1	01 = Pull- down	11 = Pullup and Down
3	OE1_term1	OE1 Pullup or down	RW	0	00 =None	10 = Pullup
2	OE1_term0	OE1 Pullup or down	RW	1	01 = Pull- down	11 = Pullup and Down
1	OE0_term1	OE0 Pullup or down	RW	0	00 = None	10 = Pullup
0	OE0_term0	OE0 Pullup or down	RW	1	01 = Pull- down	11 = Pullup and Down
Byte 1	5: OE Termination Co	ntrol				
Bit	Control Function	Description	Туре	Power-up Condition	0	1
7	OE7_term1	OE7 Pullup or down	RW	0	00 = None	10 = Pullup
6	OE7_term0	OE7 Pullup or down	RW	1	01 = Pull- down	11 = Pullup and Down
5	OE6_term1	OE6 Pullup or down	RW	0	00 = None	10 = Pullup
4	OE6_term0	OE6 Pullup or down	RW	1	01 = Pull- down	11 = Pullup and Down
3	OE5_term1	OE5 Pullup or down	RW	0	00 = None	10 = Pullup
2	OE5_term0	OE5 Pull up or down	RW	1	01 = Pull- down	11 = Pullup and Down
1	OE4_term1	OE4 Pullup or down	RW	0	00 = None	10 = Pullup
0	OE4_term0	OE4 Pullup or down	RW	1	01 = Pull- down	11 = Pullup and Down
Byte 10	5: Power Good Termir	nation Control				
Bit	Control Function	Description	Туре	Power-up Condition	0	1
7:2	Reserved			0x09		
1	PWRGD_PD1	Clock Power Good and Power Down Pullup or	RW	1	00 = None	10 = Pullup
0	PWRGD_PD0	Pulldown	RW	0	01 = Pull- down	11 = Pullup and Down
Byte 1	7: Reserved					



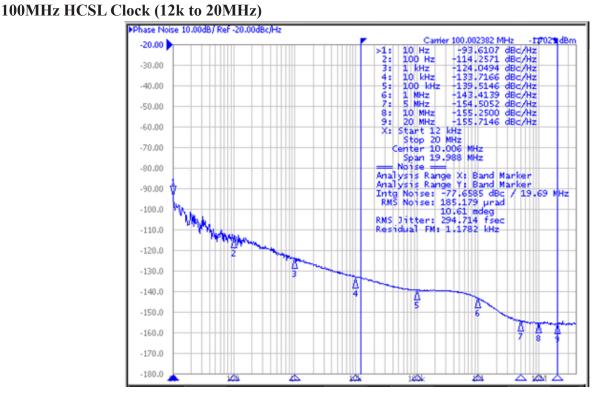


Byte 1	8: Enable Pin Control					
Bit	Control Function	Description	Туре	Power-up Condition	0	1
7	OE7_Enable	Sets Enable High or Low	RW	0	Enable = Low	Enable = High
6	OE6_Enable	Sets Enable High or Low	RW	0	Enable = Low	Enable = High
5	OE5_Enable	Sets Enable High or Low	RW	0	Enable = Low	Enable = High
4	OE4_Enable	Sets Enable High or Low	RW	0	Enable = Low	Enable = High
3	OE3_Enable	Sets Enable High or Low	RW	0	Enable = Low	Enable = High
2	OE2_Enable	Sets Enable High or Low	RW	0	Enable = Low	Enable = High
1	OE1_Enable	Sets Enable High or Low	RW	0	Enable = Low	Enable = High
0	OE0_Enable	Sets Enable High or Low	RW	0	Enable = Low	Enable = High
Byte 1	9: Power Down Pin Co	ontrol				
Bit	Control Function	Description	Туре	Power-up Condition	0	1
7:1	Reserved			0		
0	PWRGD_PD	PWRGD_PD Active via Pullup or Pulldown	RW	0	Power Down = Low	Power Down = High

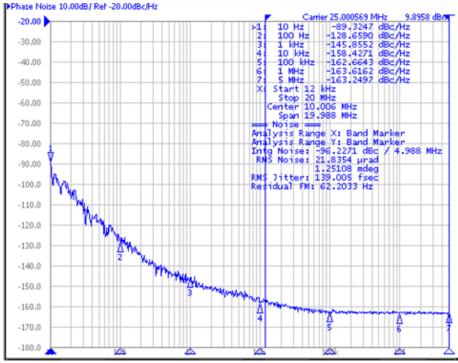




### **Plots**



## 25MHz CMOS Clock







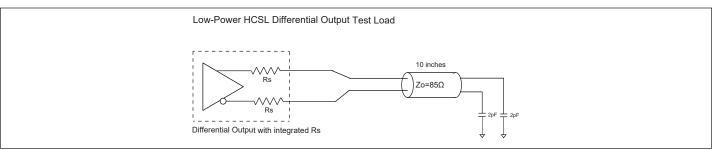
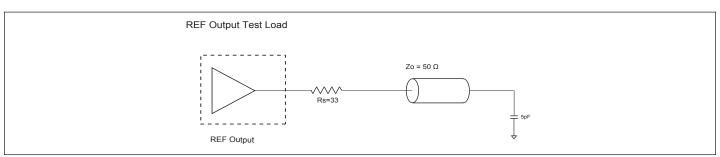


Figure 1. Low-Power HCSL Test Circuit



## Figure 2. CMOS REF Test Circuit

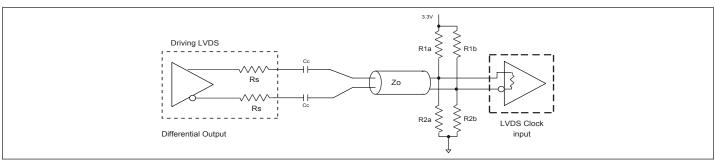
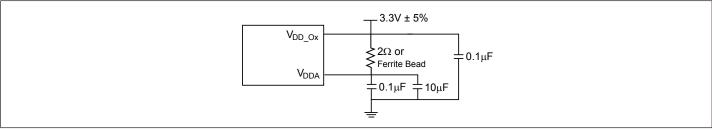


Figure 3. Differential Output Driving LVDS

## Table 3. Alternate Differential Output Terminations ( $Zo = 85\Omega$ )

Component	Receiver with Termination	Receiver without Termination	Unit
$R_{1a}, R_{1b}$	10,000	130	Ω
R <sub>2a</sub> , R <sub>2b</sub>	5600	64	Ω
C <sub>C</sub>	0.1	0.1	μF
V <sub>CM</sub>	1.2	1.2	V



## **Figure 4. Power Supply Filter**

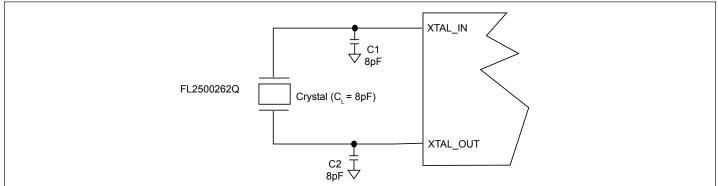




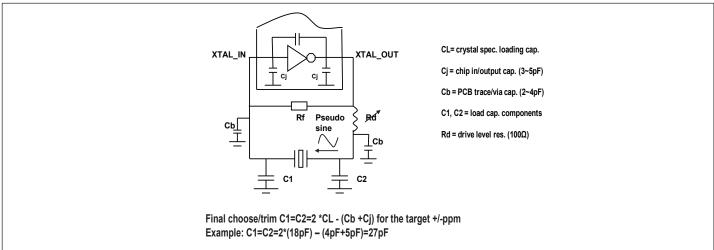
## **Crystal Circuit Connection**

The following diagram shows PI6CG33802C crystal circuit connection with a parallel crystal. For the CL= 8pF crystal, it is suggested to use C1 = 8pF and C2 = 8pF. C1 and C2 can be adjusted to fine tune to the target ppm of crystal oscillator according to different board layouts based on the following formular in the Crystal Capacitor Calculation diagram.

## **Crystal Oscillator Circuit**



## **Crystal Capacitor Calculation**



## **Recommended Crystal Specification**

#### **Diodes Recommends:**

- a) FL2500217, SMD 3.2x2.5(4P), 25MHz, CL=8pF, +/-20ppm, https://www.diodes.com/assets/Datasheets/FL.pdf
- b) FH2500016, SMD 2.5x2.0(4P), 25MHz, CL=8pF, +/-30ppm, https://www.diodes.com/assets/Datasheets/FH.pdf
- c) FW2500031, SMD 2.0x1.6(4P), 25MHz, CL=8pF, +/-30ppm, https://www.diodes.com/assets/Datasheets/FW.pdf
- d) US2500003, SMD 1.6x1.2(4P), 25MHz, CL=12pF, +/-30ppm, https://www.diodes.com/assets/Datasheets/US.pdf

Symbol	Parameter	Conditions	Min.	Тур.	Max.	Unit
$\theta_{JA}$	Thermal Resistance Junction to Ambient	Still air			38.15	°C/W
θ <sub>JC</sub>	Thermal Resistance Junction to Case				24.66	°C/W



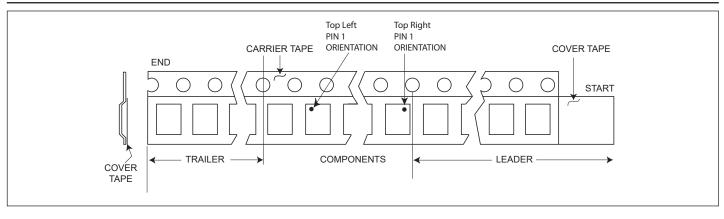


## **Part Marking**



YY: Year WW: Workweek 1st X: Assembly Code 2nd X: Fab Code

## **Package Information**

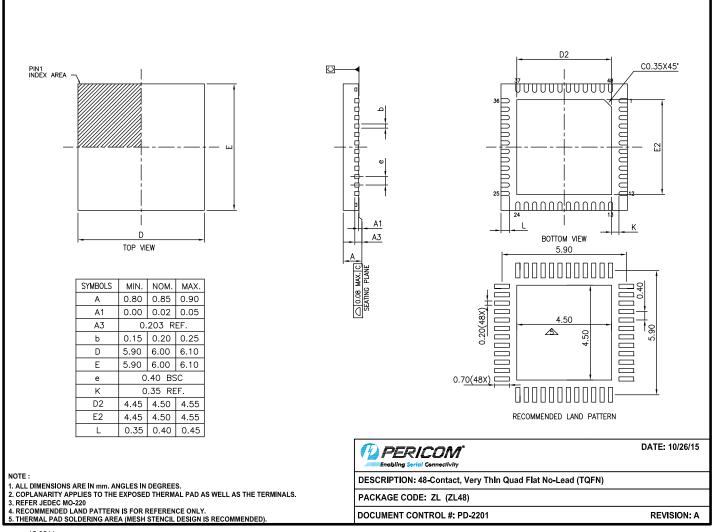






## **Packaging Mechanical**

#### **48-TQFN (ZL)**



15-0244

For latest package information:

See http://www.diodes.com/design/support/packaging/pericom-packaging/packaging-mechanicals-and-thermal-characteristics/.

## **Ordering Information**

Ordering Code	Package Code	Package Description	Pin 1 Location
PI6CG33802CZLIEX	ZL	48-Contact, Very Thin Quad Flat No-Lead (TQFN)	Top Right Corner
PI6CG33802CZLIEX-13R	ZL	48-Contact, Very Thin Quad Flat No-Lead (TQFN)	Top Left Corner

Notes:

1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS), 2011/65/EU (RoHS 2) & 2015/863/EU (RoHS 3) compliant.

2. See https://www.diodes.com/quality/lead-free/ for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free. 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm

antimony compounds.

- 4. E = Pb-free and Green
- 5. X suffix = Tape/Reel

6. For packaging details, go to our website at: https://www.diodes.com/assets/MediaList-Attachments/Diodes-Package-Information.pdf





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